

Silicon NPN Power Transistors

2SC1880

DESCRIPTION

- With TO-220C package
- DARLINGTON
- High DC current gain

APPLICATIONS

- For industrial use

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

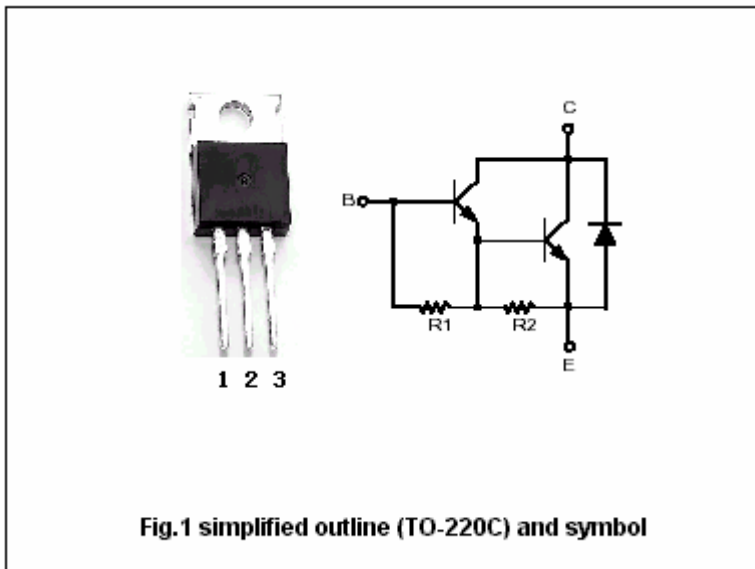


Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Tc=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	120	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	120	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current-DC		2	A
I <sub>CM</sub>	Collector current-Pulse		4	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	15	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-65~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEQ(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =30mA, I <sub>B</sub> =0	120			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =1mA, I <sub>E</sub> =0	120			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =50mA, I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =2A, I <sub>B</sub> =8mA			1.2	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =100V, I <sub>E</sub> =0			0.1	mA
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> =100V, I <sub>B</sub> =0			0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			50	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =2A ; V <sub>CE</sub> =2V	1000			

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PACKAGE OUTLINE

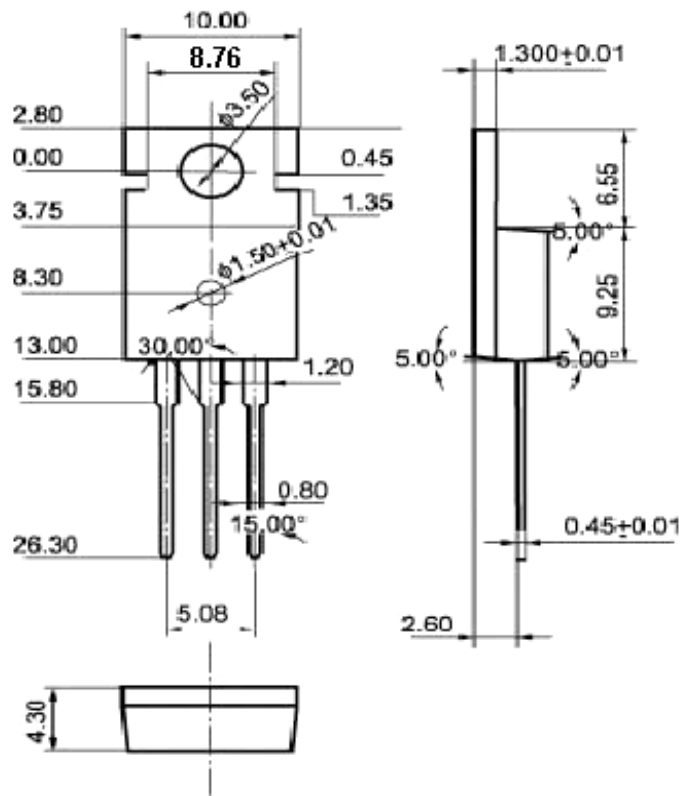


Fig.2 Outline dimensions